HSU276

Silicon Schottky Barrier Diode for Mixer

HITACHI

ADE-208-078F(Z)
Rev 6
June 1996

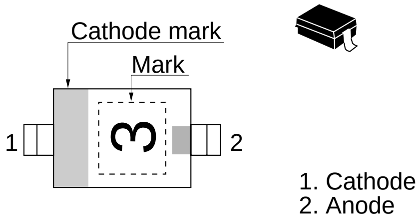
Features

- High forward current, Low capacitance.
- Ultra small Resin Package (URP) is suitablefor high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSU276	3	URP

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	VR	3	V
Average rectified current	IO	30	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55Å`+125	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	VR	3	Å\	Å\	V	IR = 1 mA
Reverse current	IR	Å\	Å\	50	µA	VR = 0.5V
Forward current	IF	35	Å\	Å\	mA	VF = 0.5V
Capacitance	C	Å\	Å\	0.85	pF	VR = 0.5V, f = 1 MHz
ESD-Capability*1	Å\	30	Å\	Å\	V	C=200pF , Both forward and reverse direction 1 pulse.

Notes 1. Failure criterion ; IR ≥ 100µA at VR =0.5 V

Main Characteristic

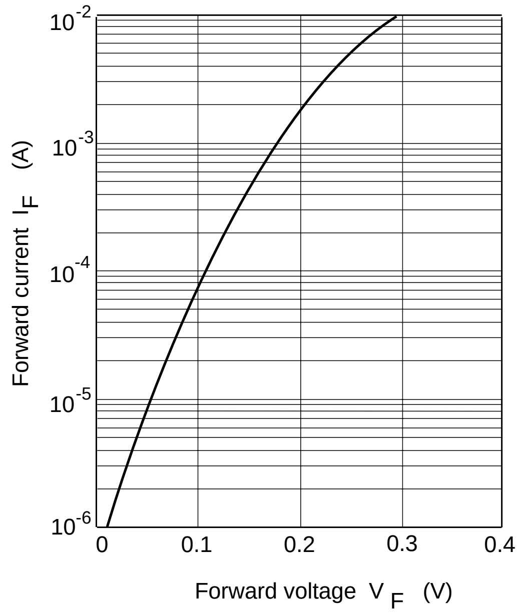

Fig.1 Forward current Vs. Forward voltage

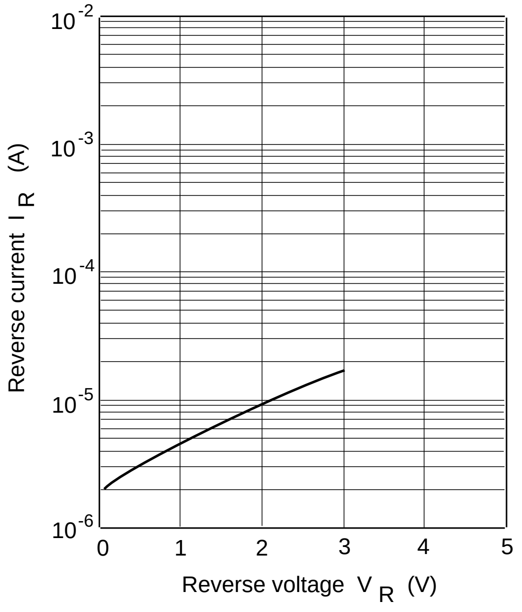

Fig.2 Reverse current Vs. Reverse voltage

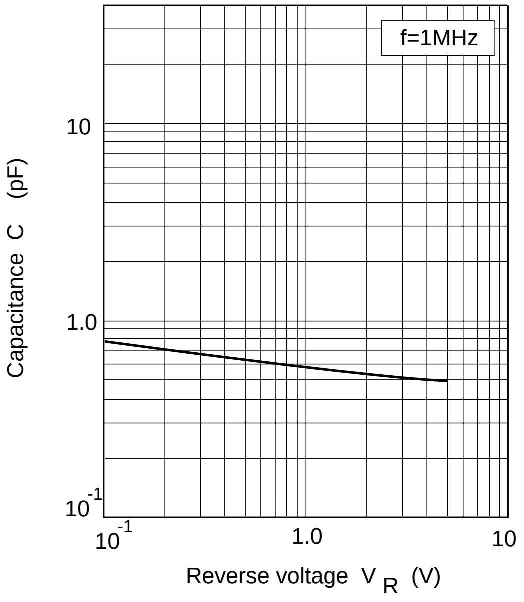

Fig.3 Capacitance Vs. Reverse voltage

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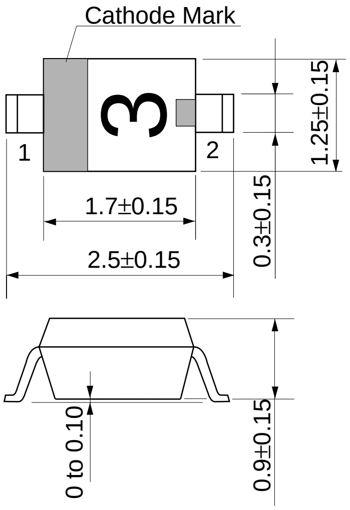
Package Dimensions

Unit : mm



1. Cathode
2. Anode

Hitachi Code	URP
JEDECCode	—
EIAJCode	—
Weight(g)	0.004